

# Welcome!

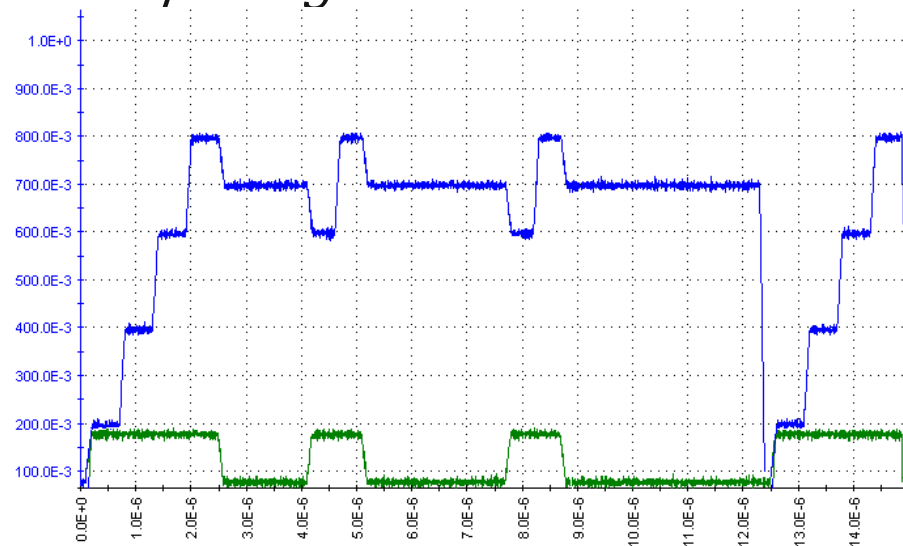
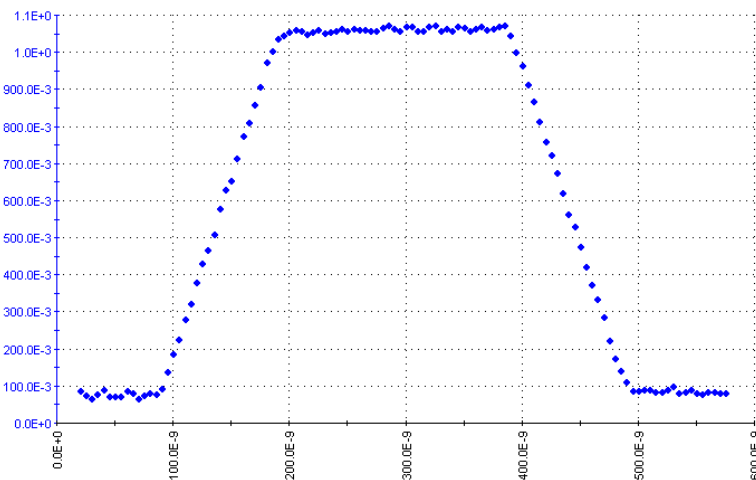
## **Device Characterization with the Keithley Model 4200-SCS Characterization System**

# Ultra-Fast I-V for Pulsed and Transient Characterization



# Ultra Fast I-V

- **Ultra Fast I-V means any test that requires**
  - short pulses or transitions between voltages ( $< 10 \mu\text{s}$ )
  - Multi-level waveforms (examples: Flash testing or ultra fast BTI)
  - High-speed measurements *while pulsing*



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# Ultra Fast I-V Hardware (1/2)

- **Model 4225-PMU – Ultra Fast I-V**
  - 2 channels of voltage pulsing with integrated simultaneous V and I measurement on each channel
  - Uses single slot in 4200 Chassis
  - Up to 4 cards per chassis (leaving 5 slots available for SMUs and CVU)
- **Pulse from mV to 40V (into high impedance)**
- **Pulse widths from 60 ns to 999 ms**
- **Control timing parameters**
  - Pulse Delay
  - Pulse Width
  - Rise Time and Fall Time
  - Pulse Period



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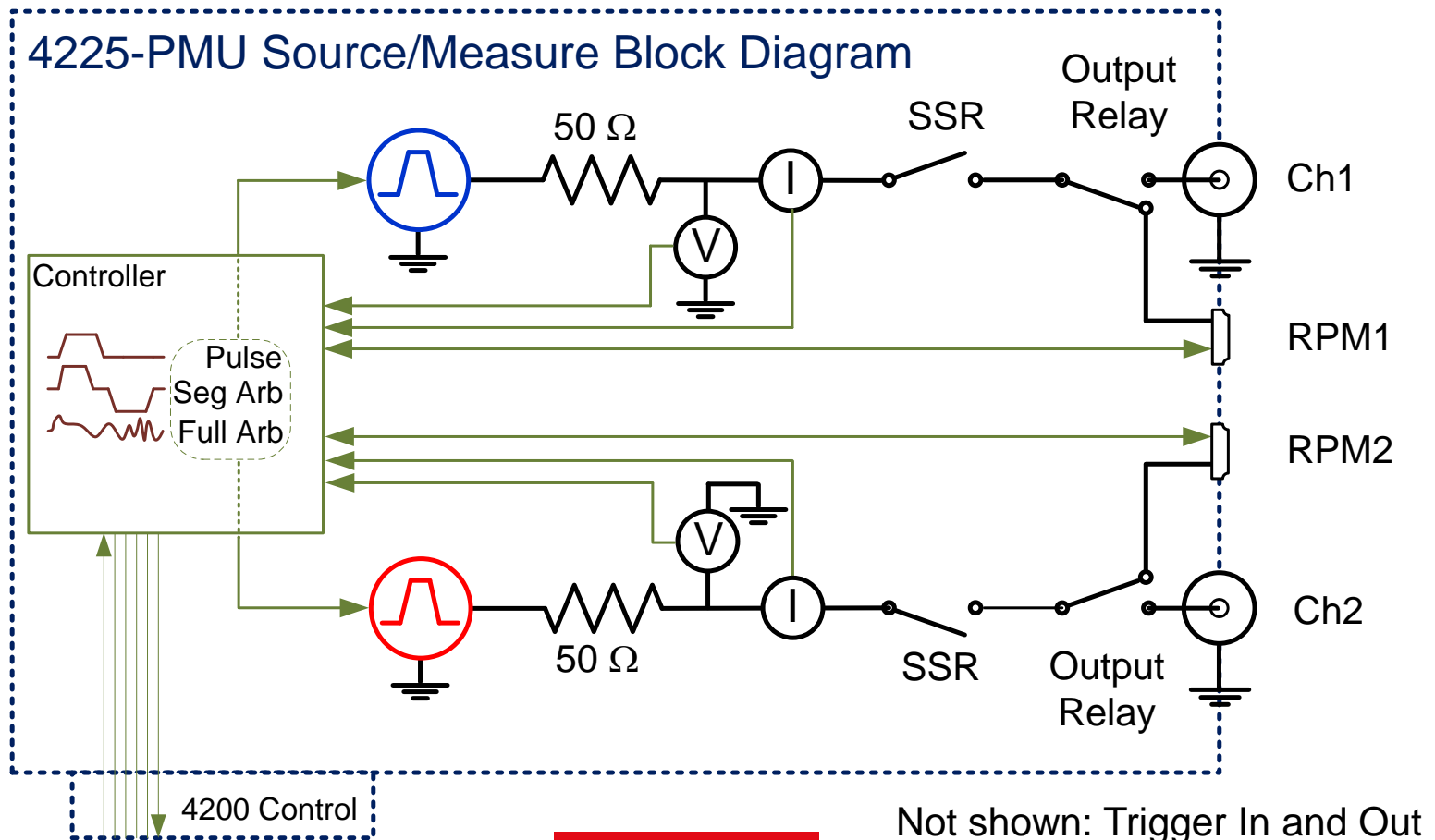
## Optional 4225-RPM Remote Amplifier/Switch

- **Optional Remote Amplifier Switch (4225-RPM)**
  - reduces cable effects, adds low current measure ranges
  - Measure signals to  $<5$  nA
- **4225-RPM also acts as SMU/PMU/CVU switch matrix**
  - Simplifies test set ups, quicker testing
  - No re-cabling when moving between test types
    - SMU
    - CV
    - Pulse IV



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# 4225-PMU Block Diagram



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Not shown: Trigger In and Out

## Ultra-fast IV applications require different capabilities

	Voltage	Max Current	Min Current	Rise time	Pulse Width	Duty Cycle
Single Pulse Charge Trapping / High K	+/-10v	10mA	<100nA	<100nSec	50nS-1uSec	n/a
Silicon-On-Insulator / isothermal	+/-10v	10mA	<10nA	<100nSec	100nSec	0.01%-50%
LDMOS/GaAs isothermal	+/-40v	400mA	<100nA	<100nSec	200nSec	0.01%-50%
Flash	+/-40v	10mA	<10nA	100nSec	100nS-1mSec	n/a
PC-RAM	+/-10V	10mA	<100nA	<10necS	150nSec	n/a
UF NBTI	+/-10	10mA	<2nA	50nSec	<1uSec	n/a
Thermal Impedance	+/-40V	400mA	1uA	<1uSec	1uS-1Sec	0.1%-50%
RTS	+/-40V	10mA	<10nA	n/a	100nS-1mSec	n/a
CBCM	+/-10V	10mA	100nA	1uSec	1uS-10mSec	1%-50%

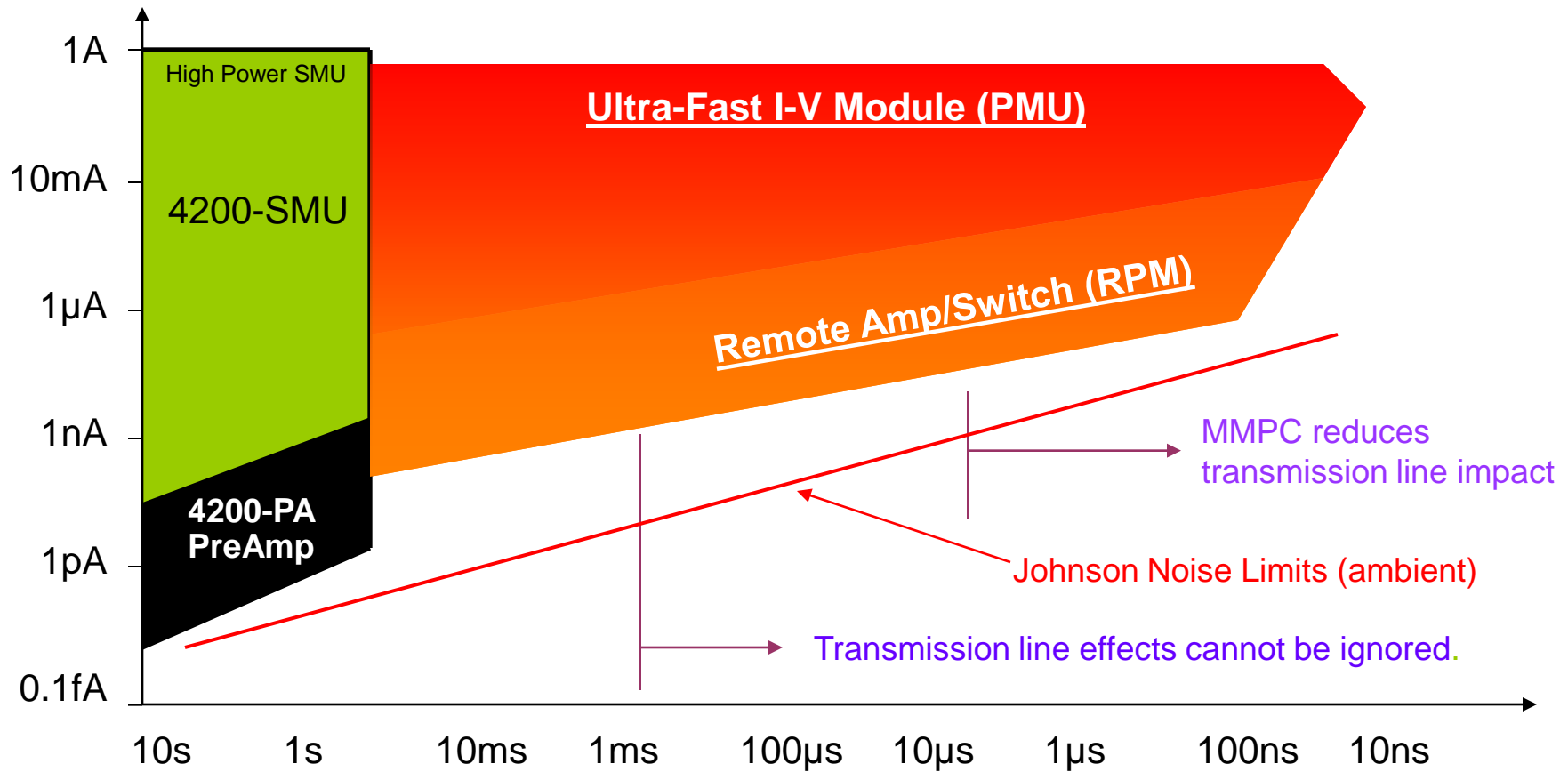
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# Difference between DC and Ultra Fast I-V?

- **What are the main differences between a 4200 SMU and the 4225-PMU?**
- **DC I/V – Accuracy/Precision Priority**
  - Force voltage and/or current conditions on device
  - Delay until the system reaches equilibrium
  - Measure with long integration time to maximize accuracy and precision
- **Ultra-Fast I/V – Deterministic Timing Priority**
  - Force sequence is precision timed
  - Delays are limited to “time available” in sequences
  - Measurement sequence runs in “lock step” with force sequence



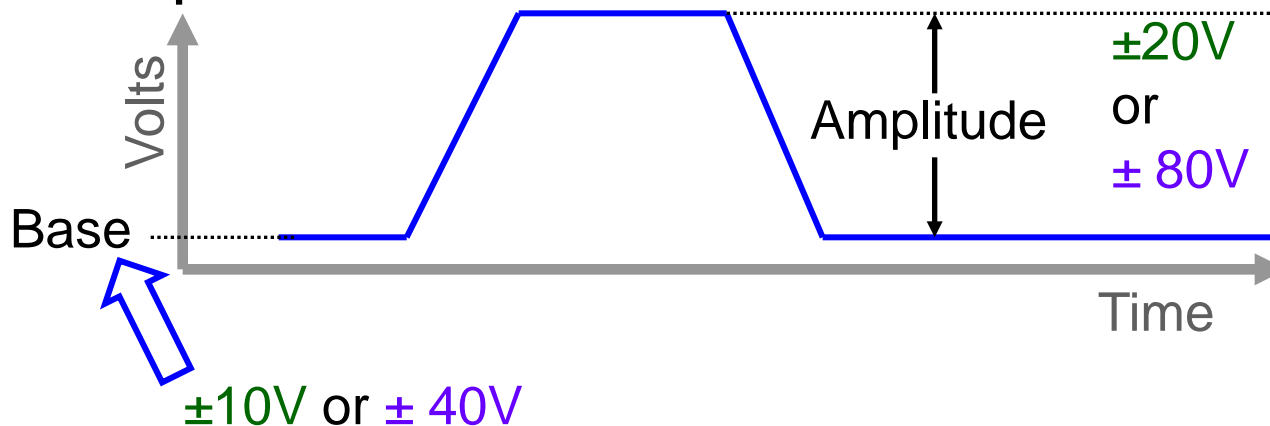
# Current vs. Time Measurement Comparison



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# Pulse Voltage

- 2 voltages to define standard (2-level) pulse
- Two PMU source ranges
  - 10V (into high impedance)
  - 40V (into high impedance)
- Base: 10V or 40V
- Amplitude: 20V or 80V

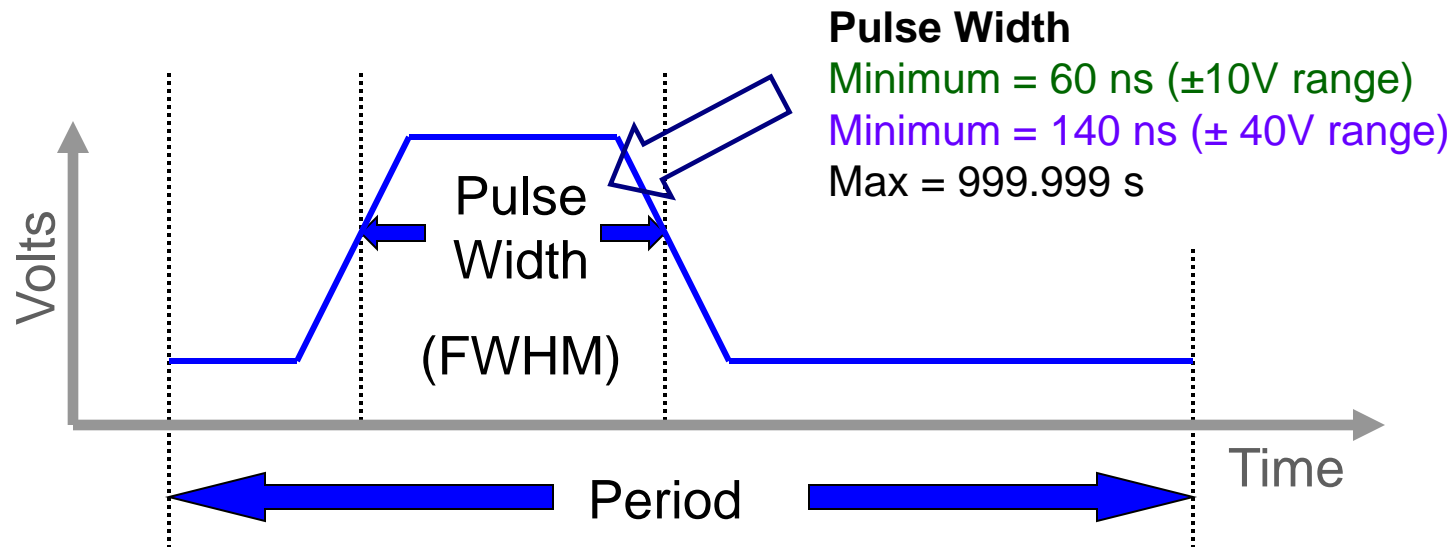


Key:  
 ±10V range  
 ±40V range

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# Pulse Timing (1/2)

- **Pulse Width is calculated at 50% amplitude**
  - Full Width at Half Maximum (FWHM)



Minimum of 120 ns for 10V range  
 Minimum of 280 ns for  $\pm 40V$  range  
 Max = 1 s

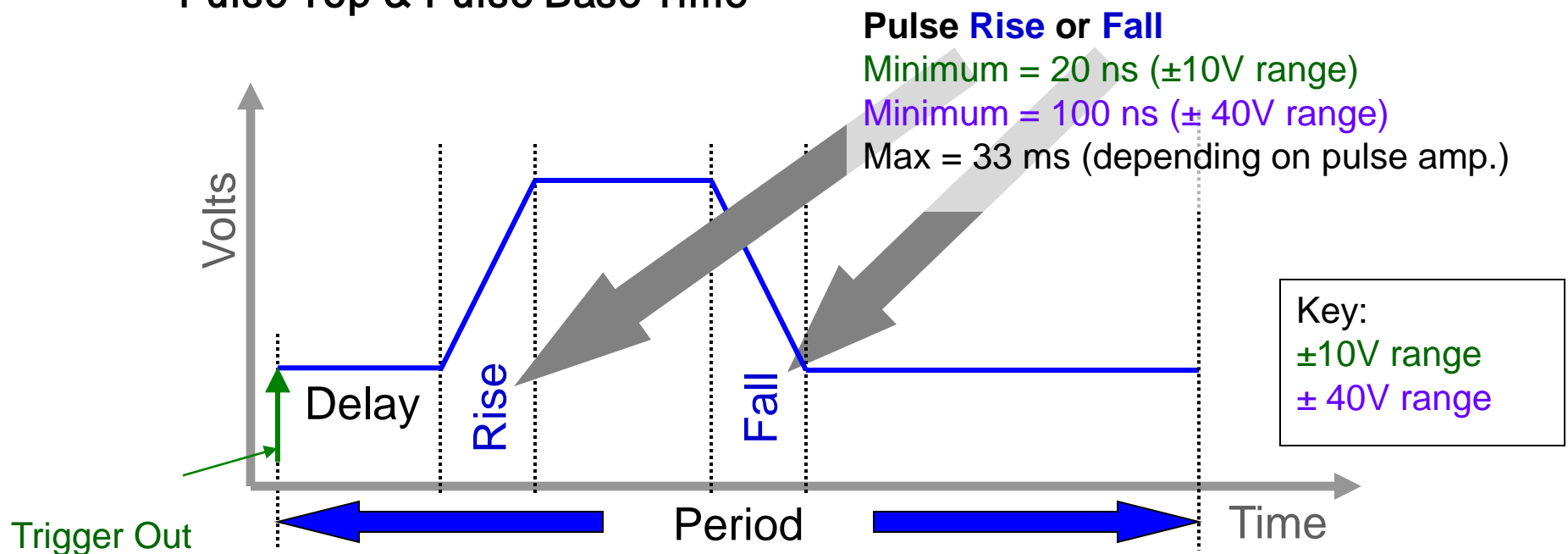
Key:  
 $\pm 10V$  range  
 $\pm 40V$  range

Timing values shown for measurement enabled.  
 Shorter minimums available for source only.

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# Pulse Timing (2/2)

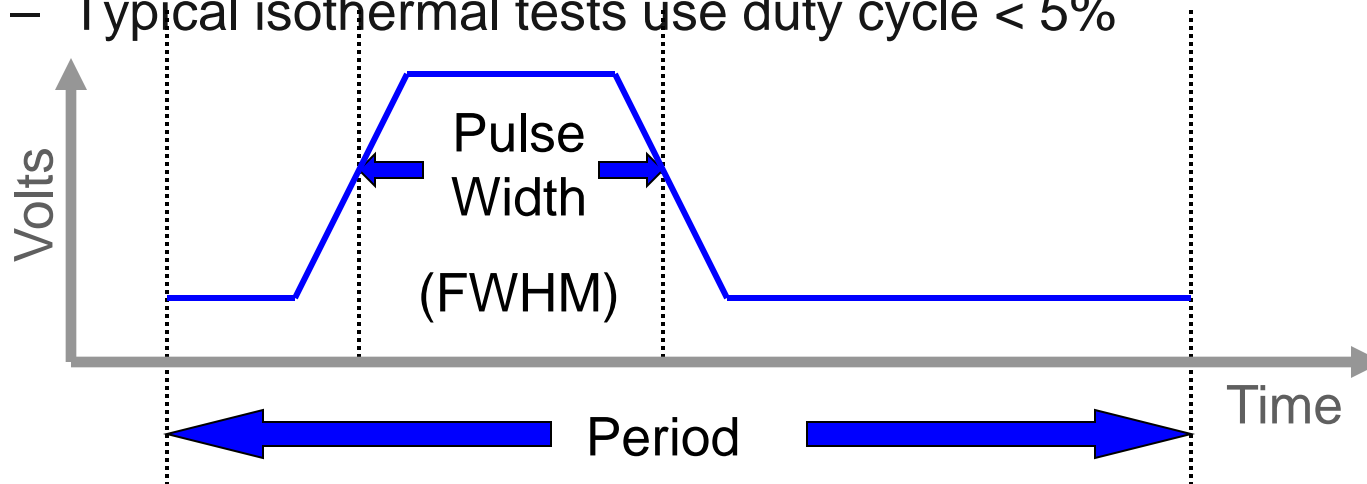
- Transitions
  - Rise and Fall are for 0-100% (Industry uses 10-90%)
- Pulse Top & Pulse Base Time



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# Duty Cycle

- **Duty Cycle = Pulse Width / Period**
  - Amount of time that the pulse is “on”
  - Typical isothermal tests use duty cycle < 5%

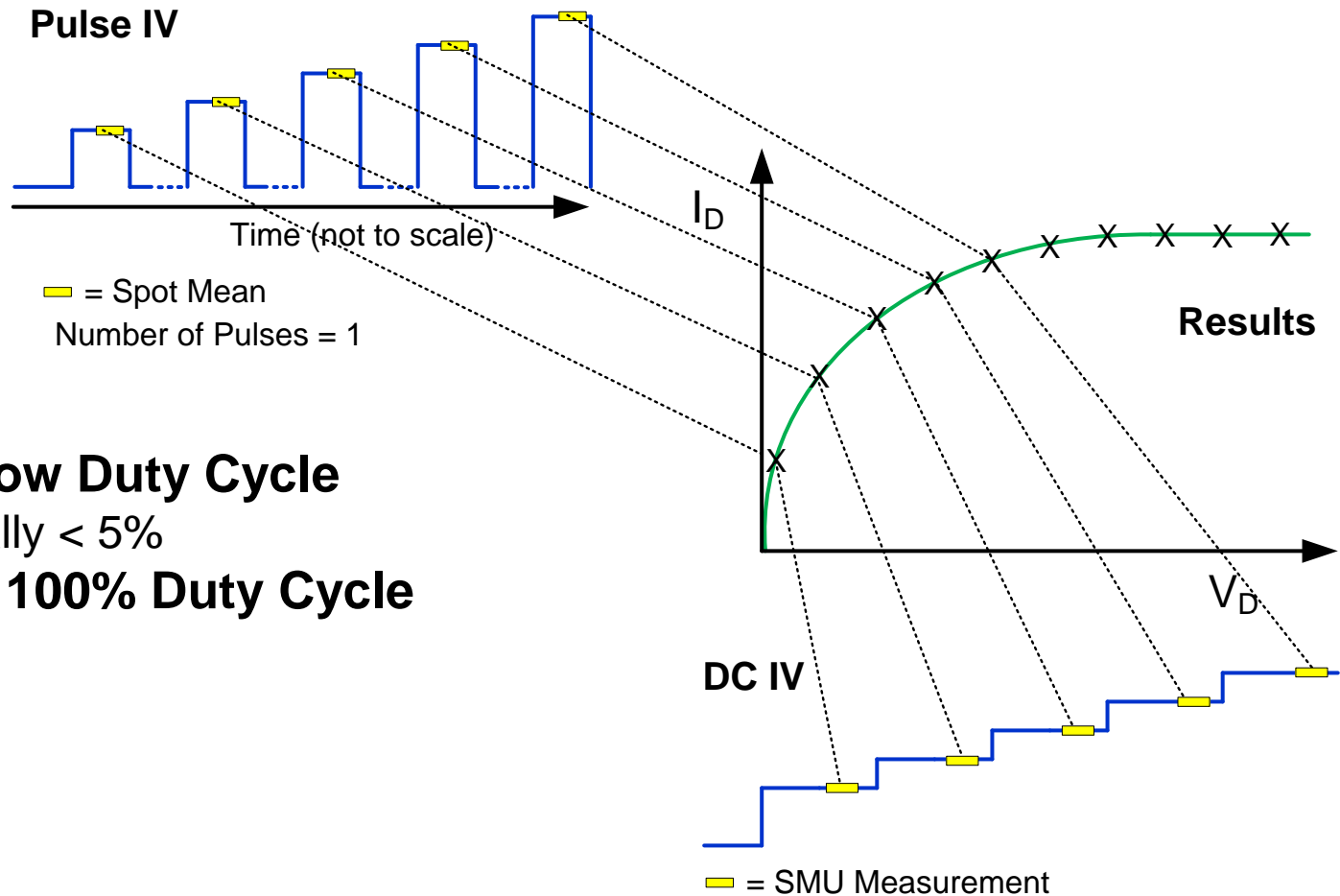


Example: 100 ns PW, 1 us Period:

$$\text{Duty Cycle} = \text{PW} / \text{Period} = 100\text{e-}9 / 1\text{e-}6 = 0.1 = 10\%$$

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# Pulse IV vs DC Testing Diagram



## Pulse IV: Low Duty Cycle

– Typically < 5%

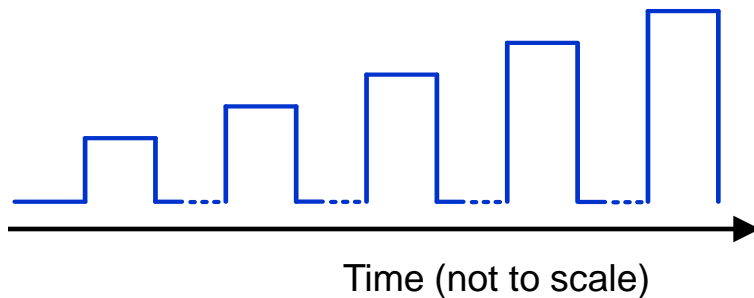
## DC testing: 100% Duty Cycle

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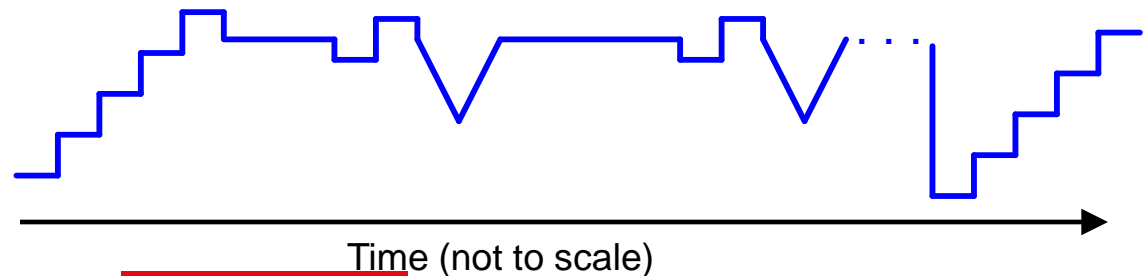
# PMU Source modes

- PMU provides Ultra-fast IV through 2 types of Source Modes
  - Standard (2-level) Pulse
  - Segment ARB™

## Standard, 2-level pulsing



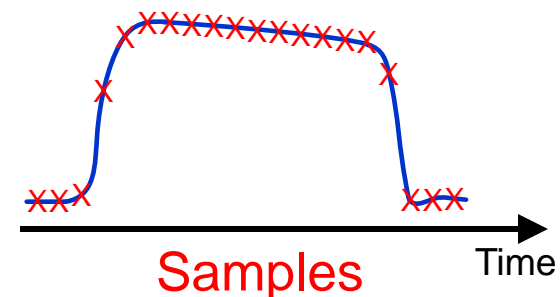
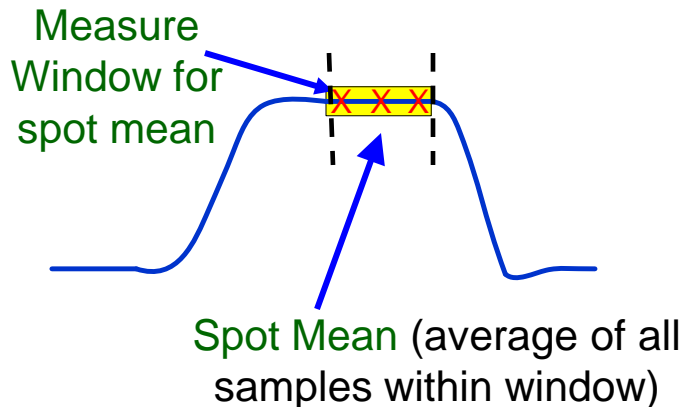
## Segment Arb



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# PMU Measure types

- PMU provides Ultra-fast IV through 2 types of Measure Types
  - **Spot Mean** – used for Pulse IV
    - Just a mean of all samples within the measure window
  - **Sample** – used for Waveform Capture
    - Individual A/D samples across the measure window
- **Averaging and Discrete**
  - When sourcing multiple pulses, can choose to average them, or keep them as individual readings



X = A/D sample

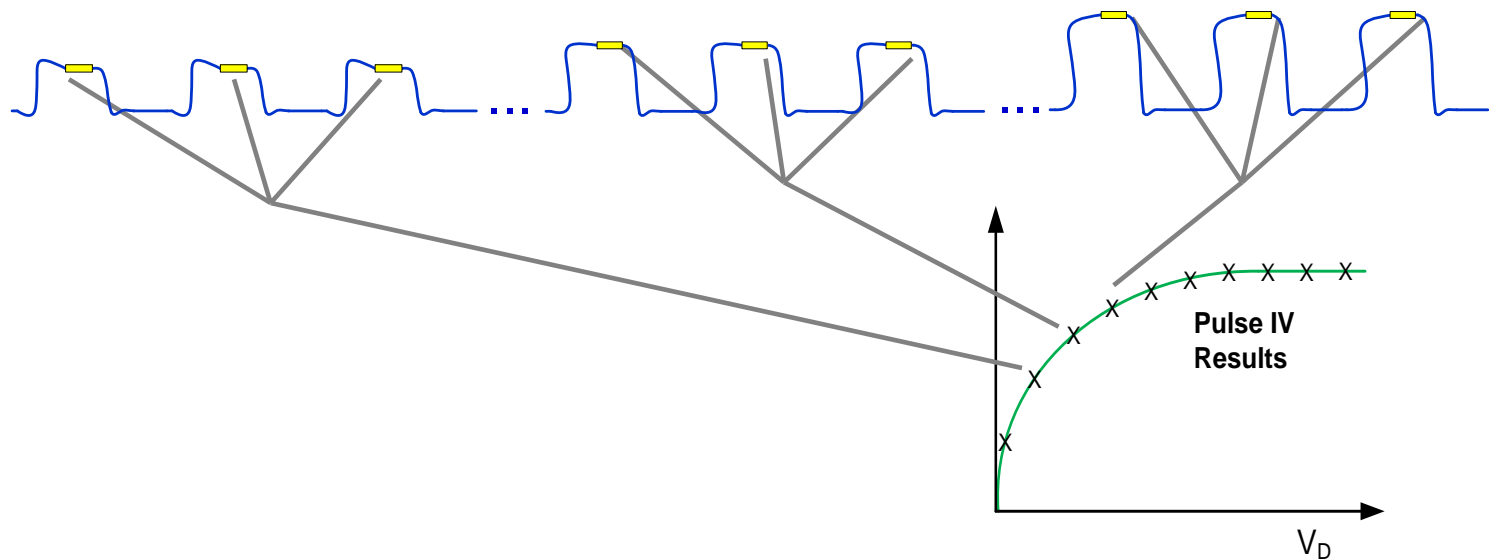
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# Tests using Spot Mean

- **Spot Mean**

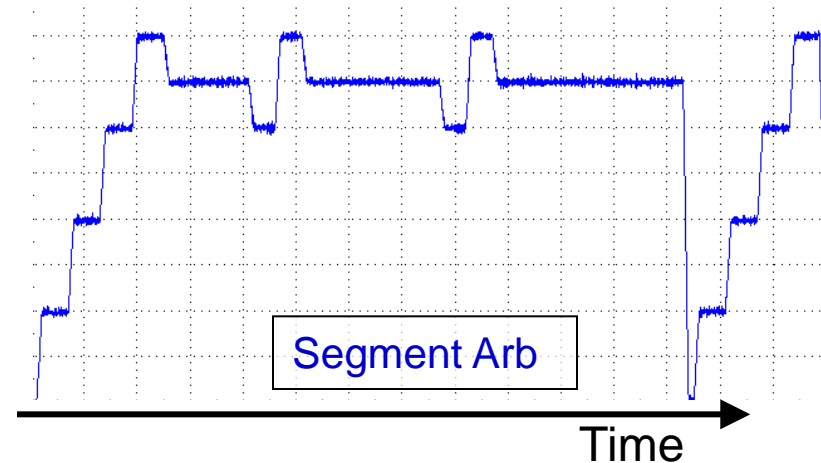
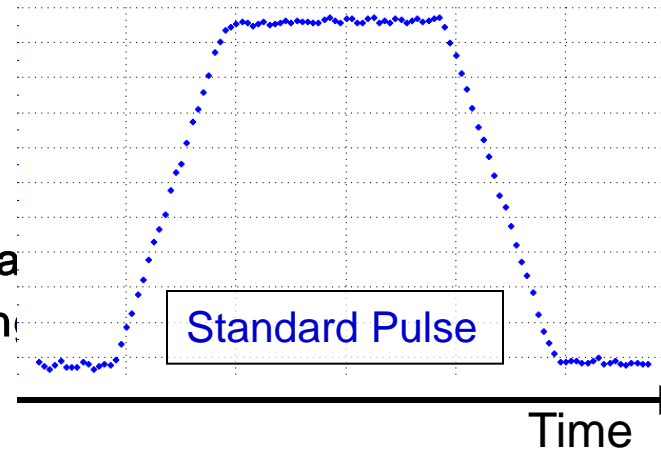
- Used for
  - IV Sweeps using standard (2-level) source mode
- Provides the mean of samples within measure window

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# Tests using Sample Measurement

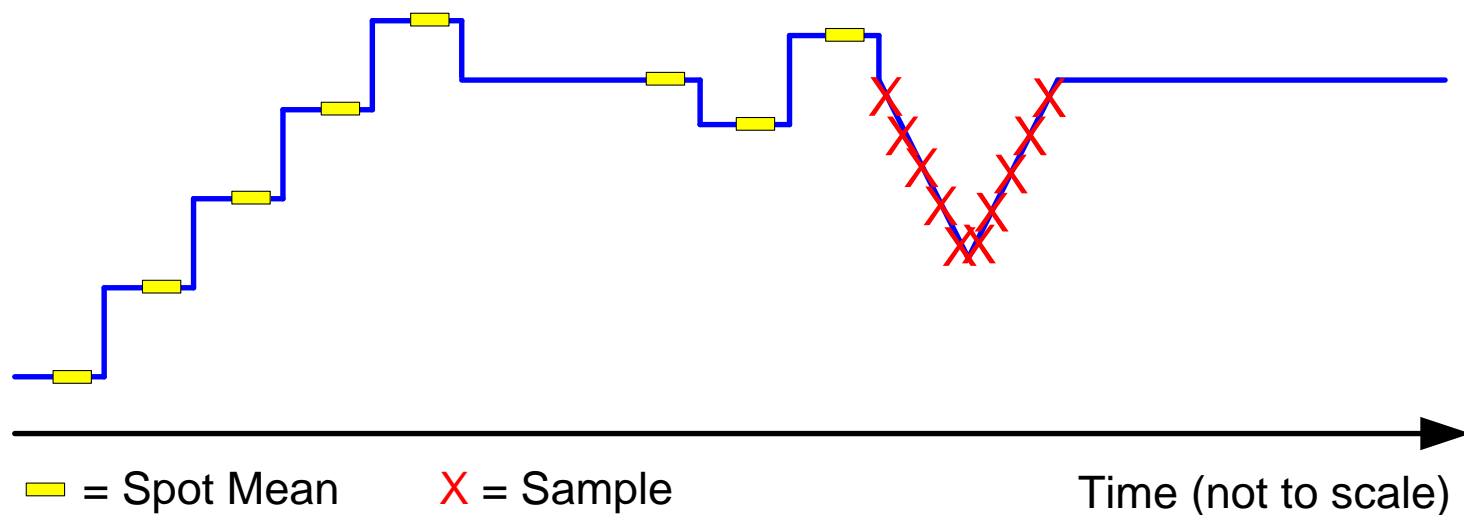
- **Sample**

- Used for
  - Waveform Capture
  - Instrument setup verification and validation
  - Pulse shape validation prior to IV testing
  - Transient IV
  - Time-resolved reliability
- Provides signal versus time data
- Maximum sample rate = 200 MSa/s
  - Sample every 5 ns
  - Minimum sample rate = 1kSa/s

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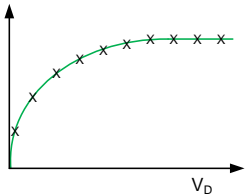
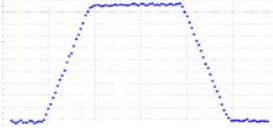
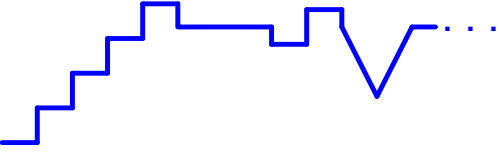
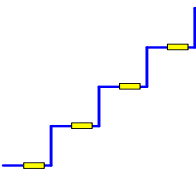
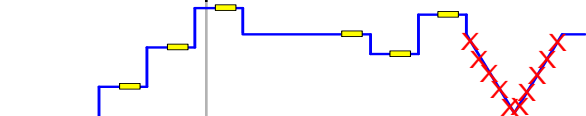
# Segment Arb supports Spot Mean and Sample

- Segment Arb allows both Spot Mean and Samples within a single waveform



Segment Arb with multiple levels, Spot Means and Sample measurements

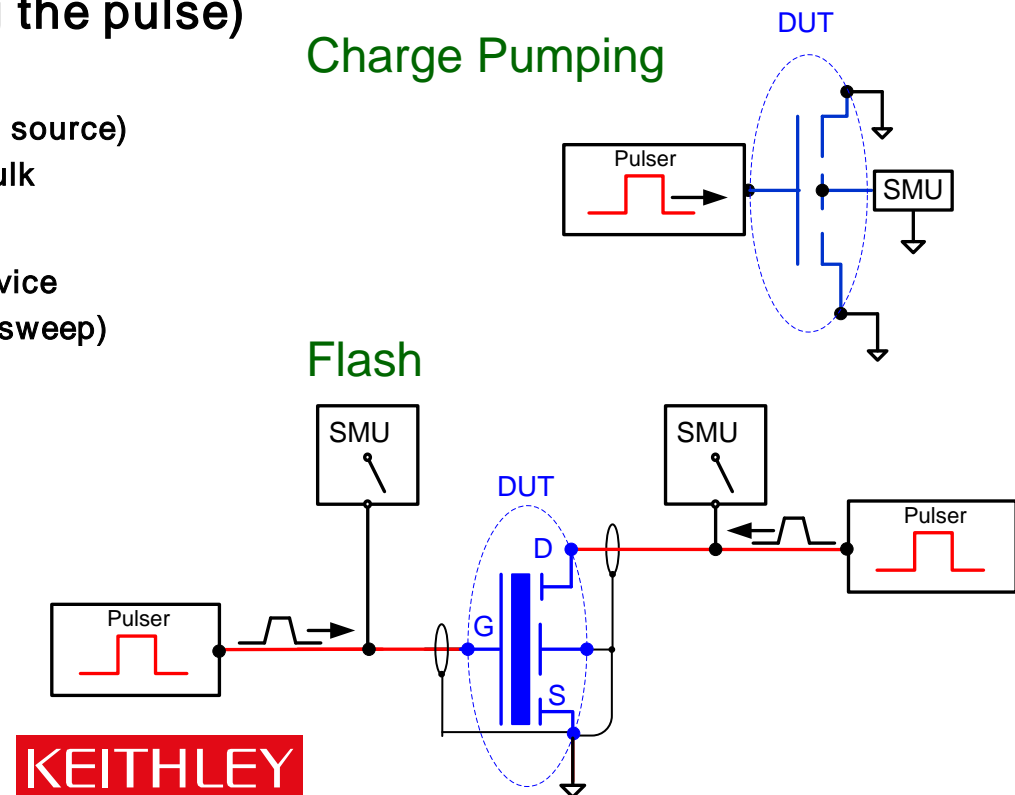
# PMU source and measure modes for UF IV

Source \ Measure	Spot Mean	Sample (waveform capture)
<p><b>2-level</b></p> 	<p><b>Pulse IV Sweeps</b></p> 	<p><b>Transient Characterization</b></p> <ul style="list-style-type: none"> <li>• Thermal effects</li> <li>• Charging effects (hysteresis)</li> </ul> 
<p><b>Segment ARB</b></p> 	<p><b>UF BTI NVM</b></p> 	<p><b>UF BTI dynamic recovery NVM Transient Characterization during program and erase</b></p> 

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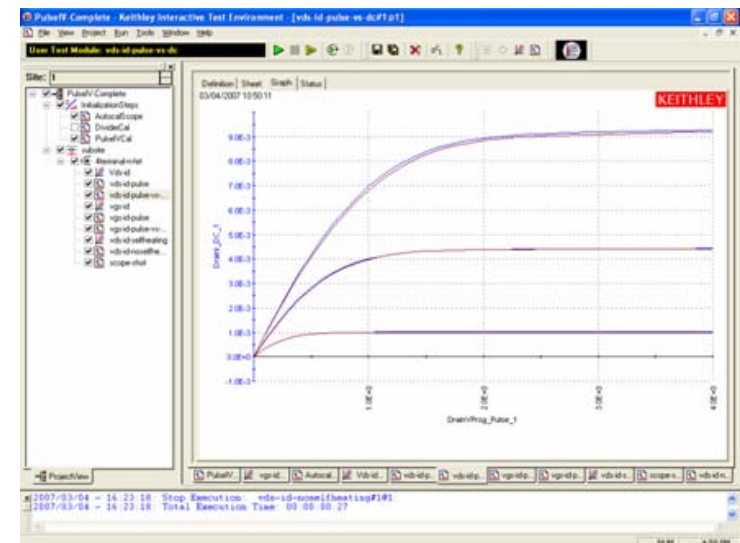
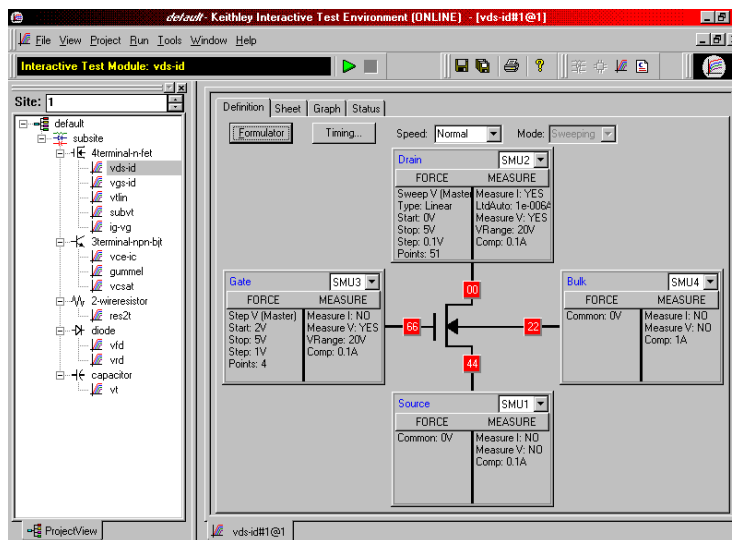
## Other Common Pulse Tests: Charge Pumping, Flash Testing

- Why are Charge Pumping and Flash testing missing from previous slide?
- Both Charge Pumping and traditional Flash testing do not require Pulse IV (no fast measuring during the pulse)
  - Charge Pumping
    - Pulse on gate (ground drain and source)
    - SMU measures DC current on bulk
  - Flash
    - Pulser to Program and Erase device
    - SMU to characterize (usually  $V_T$  sweep)



# Pulsed (or Ultra-Fast) I-V As easy as DC

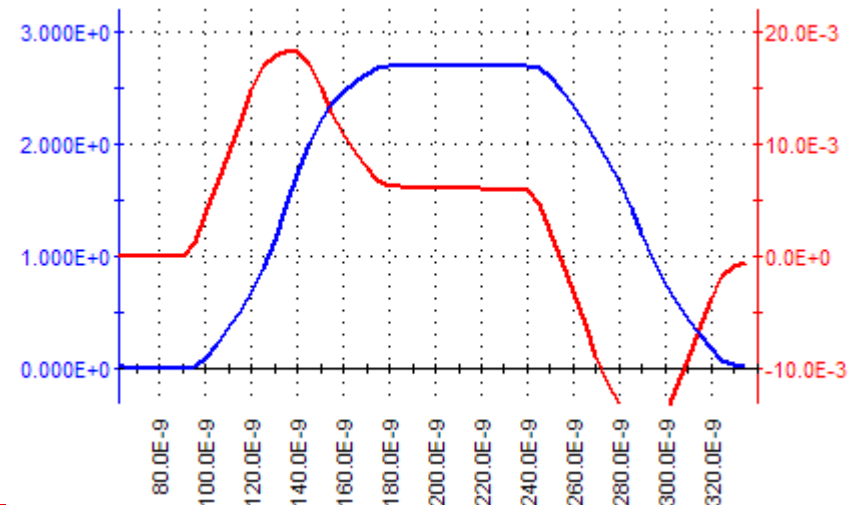
1. Connect your DUT
2. Set up the **PMUs** using KITE graphical user interface
3. Click on the green arrow
4. See the Curve and data



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# Introduction to Transient Pulse Analysis

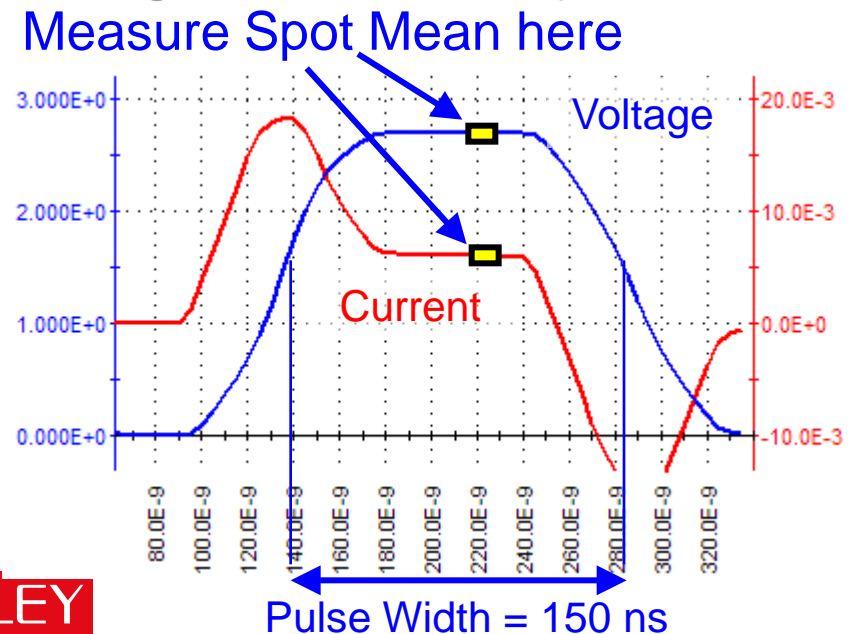
- Pulse shape determines Spot Mean value for Pulse IV Curves
- Pulse top must be settled for Pulse IV result to correlate to SMU result
- Brief introduction to current charging effects during pulse transitions



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# Why pulse shapes are important for Pulse IV

- Pulse IV sweep use measurement from settled part of pulse
  - PMU does not have any way to tell if signal is settled
  - Spot mean measure window is at the latter part of the pulse
  - If the pulse width is too short (that is, signal is not settled), a spot mean is still provided

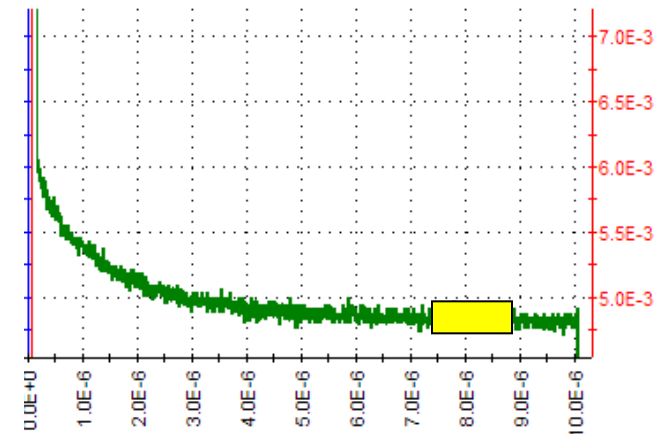
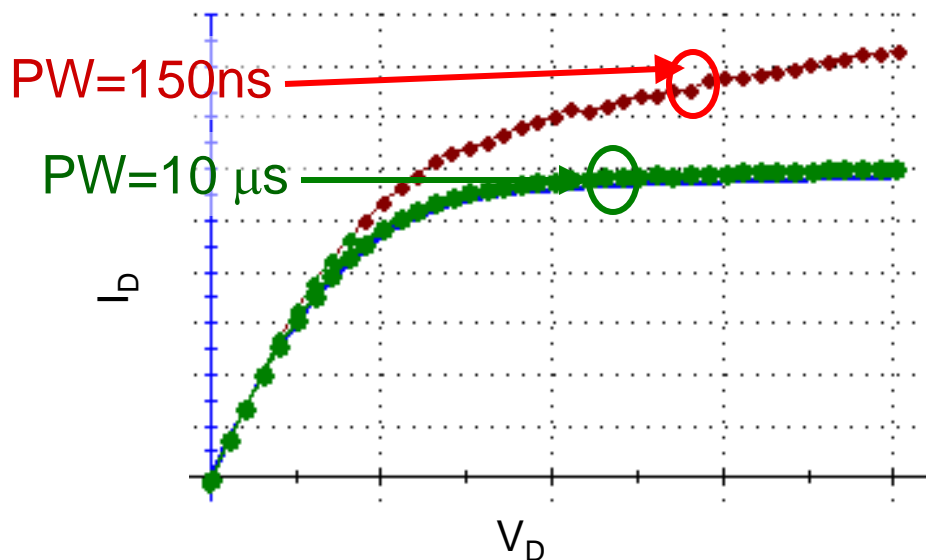


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# Pulse IV curve versus Pulse Width

- Pulse width directly effects the resulting Pulse IV Curve
- PW = 150 ns (not settled)
- PW = 10  $\mu$ s (settled)



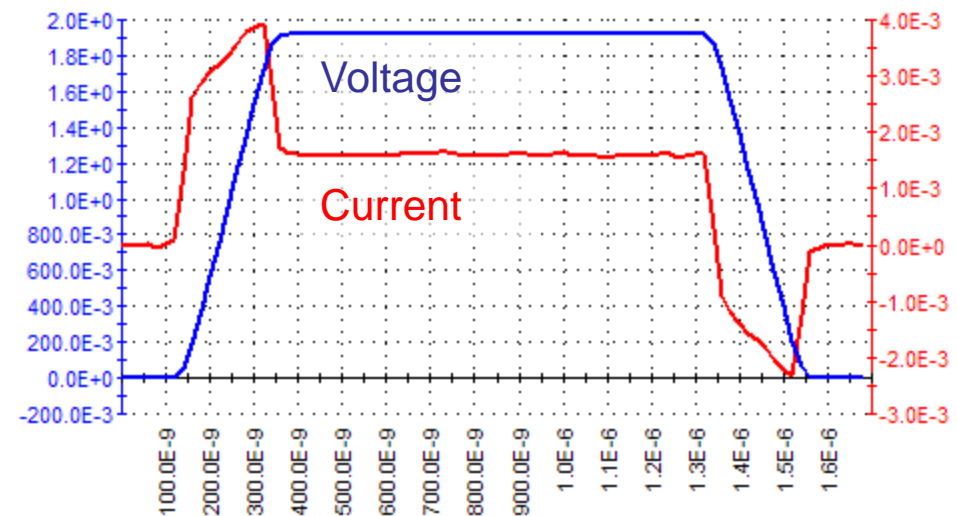
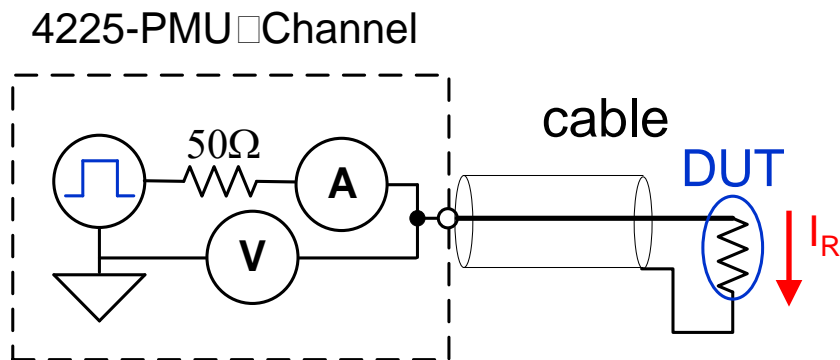
PW=10  $\mu$ s

= Spot Mean Measure Window

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# Current Waveform

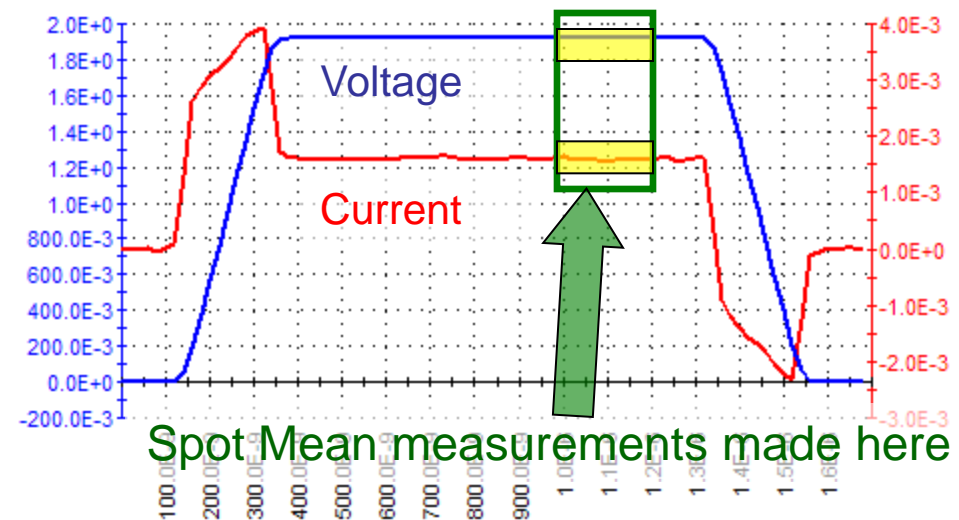
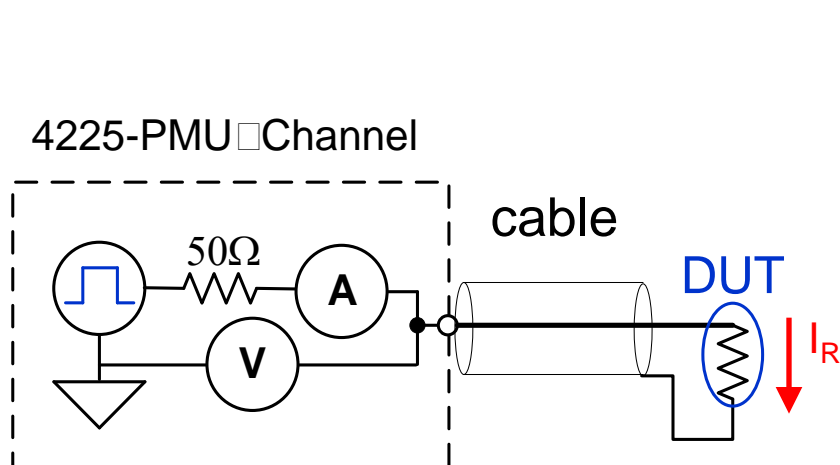
- Pulse voltage across resistor
- Measure voltage and current versus time



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# Current Waveform

- Pulse voltage across resistor
- Measure voltage and current versus time



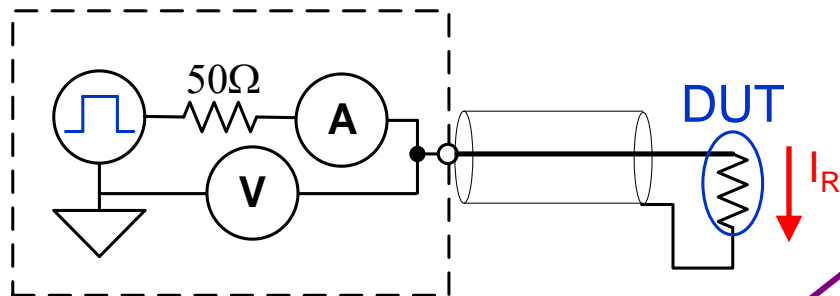
 = Spot Mean Measure Window

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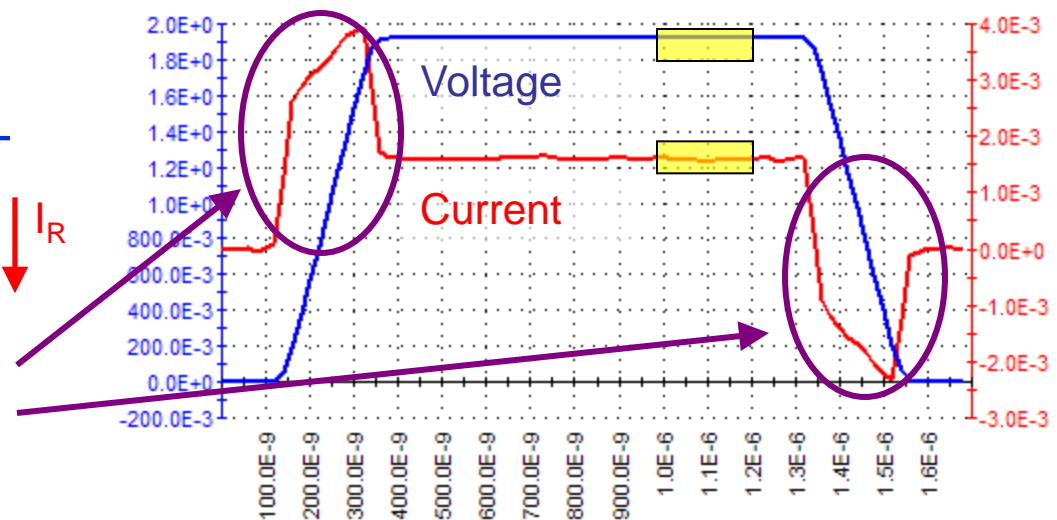
# Current Waveform

- Pulse voltage across resistor
- Measure voltage and current versus time

4225-PMU Channel



What are these features?

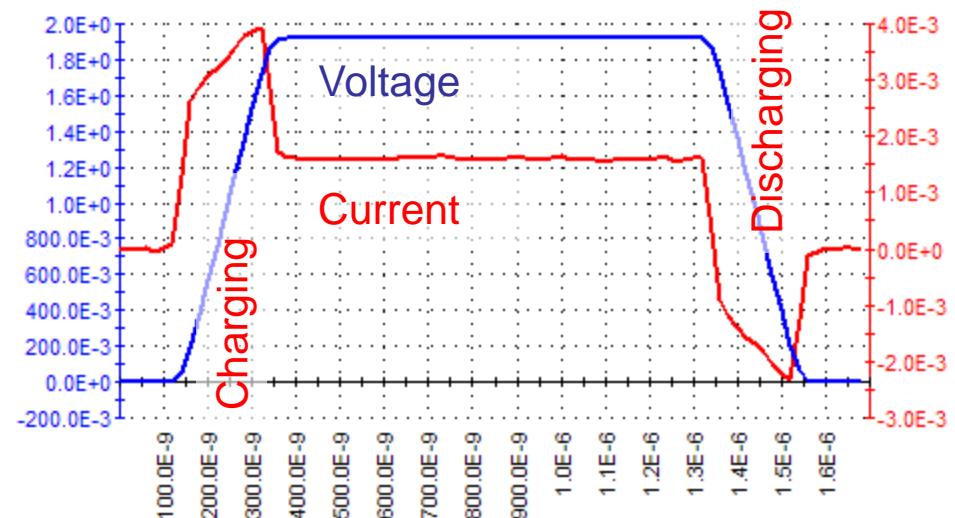
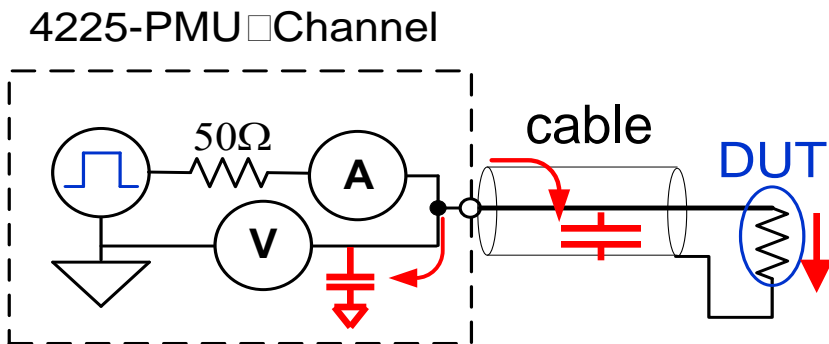


 = Spot Mean Measure Window

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# Current Charging Effects During Pulse Transitions

- During pulse rise and fall times, current charges the interconnect and instrument capacitance

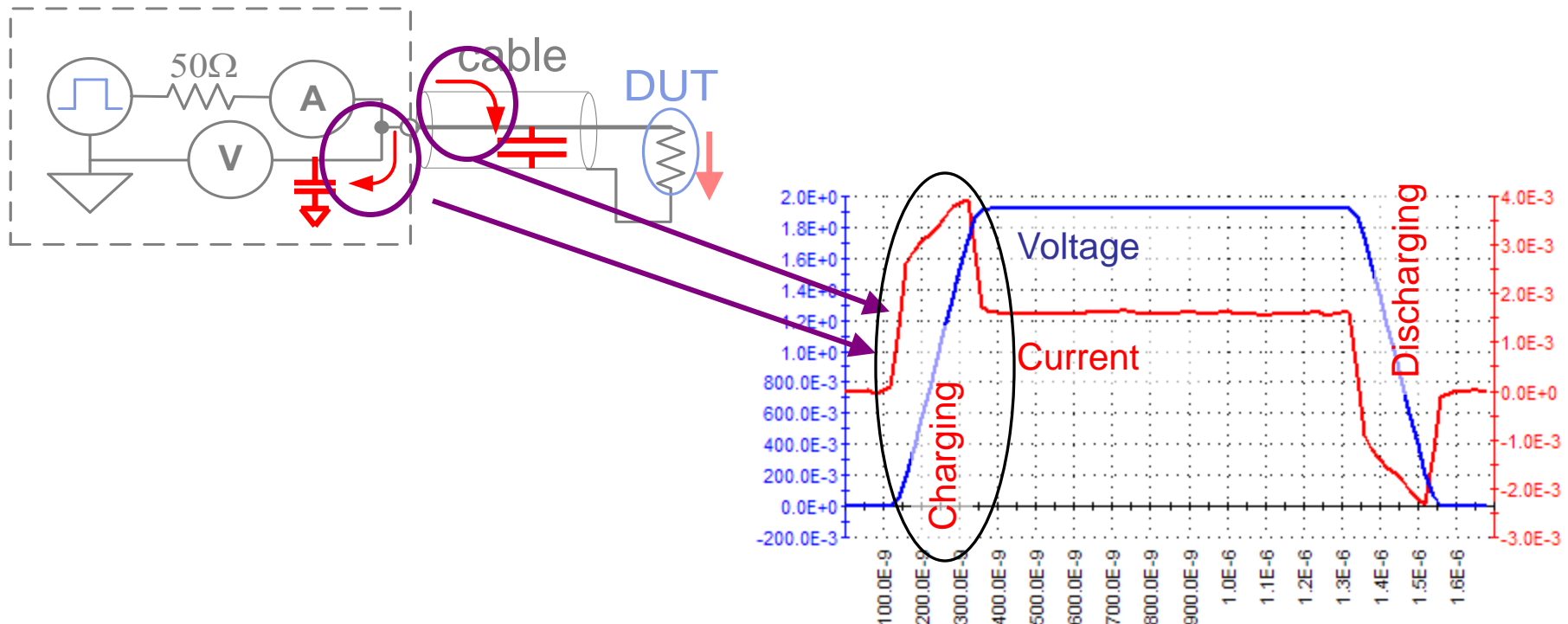


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# Current Charging Effects During Pulse Transitions

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4225-PMU Channel

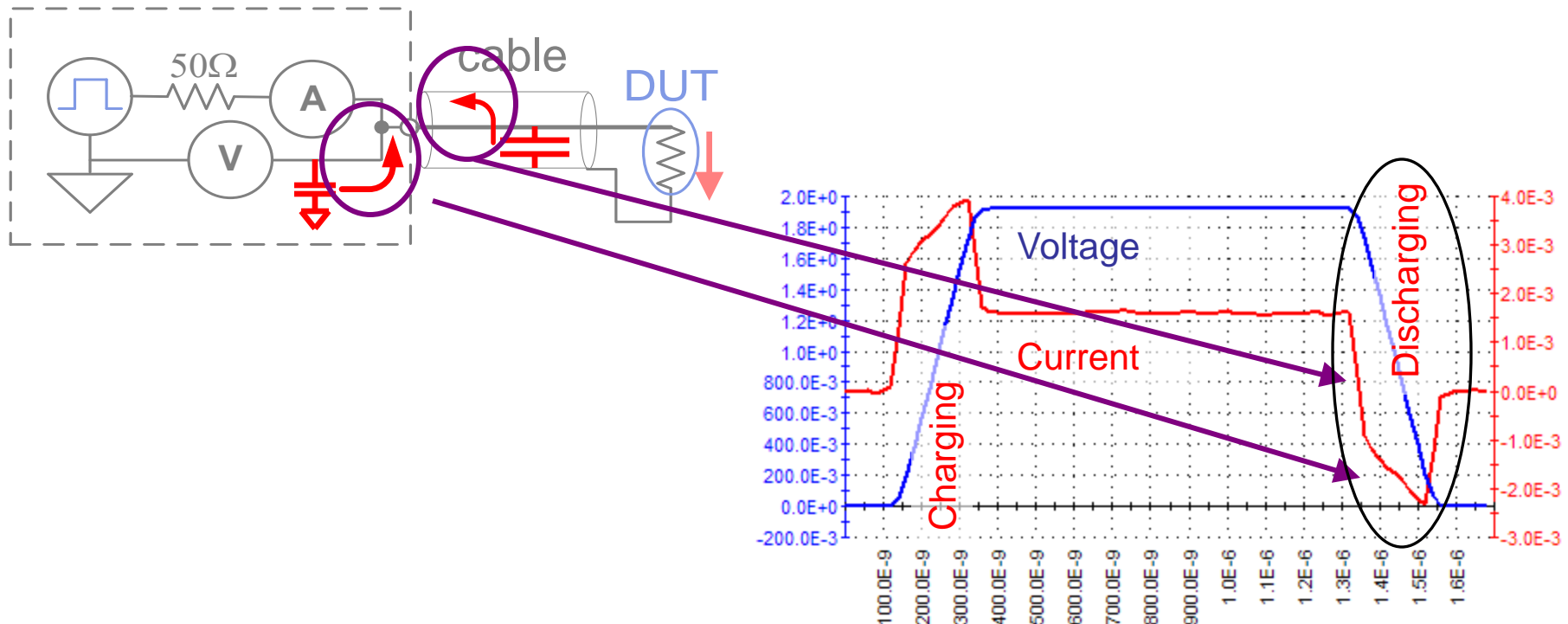


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# Current Charging Effects During Pulse Transitions

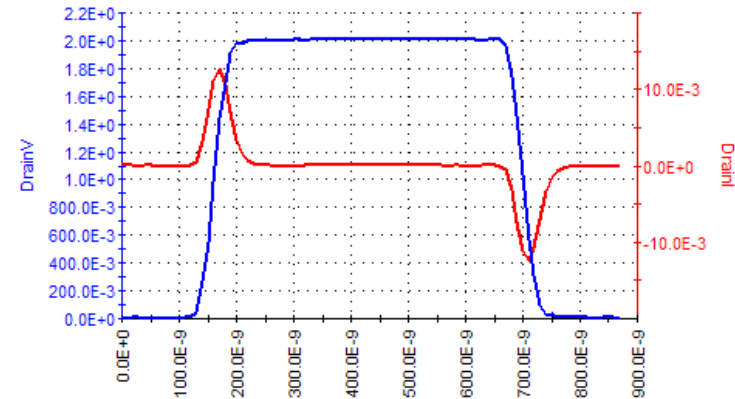
- During pulse rise and fall times, current charges the interconnect and instrument capacitance

4225-PMU Channel



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# Why haven't I seen this current charging effect before?



- **Possible reasons**

1. Oscilloscopes measure voltage not current
2. SMU measurements are made on a settled signal
3. Minimal experience with pulse waveform measurement (especially current measure waveforms)
4. Must look at pulse waveforms where current is relatively low, or DUT impedance relatively high ( $> \sim 100 \Omega$ )
5. Must use pulse transition times that are relatively fast ( $< \sim 1 \text{ us}$ )

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# Measuring Small Currents Quickly

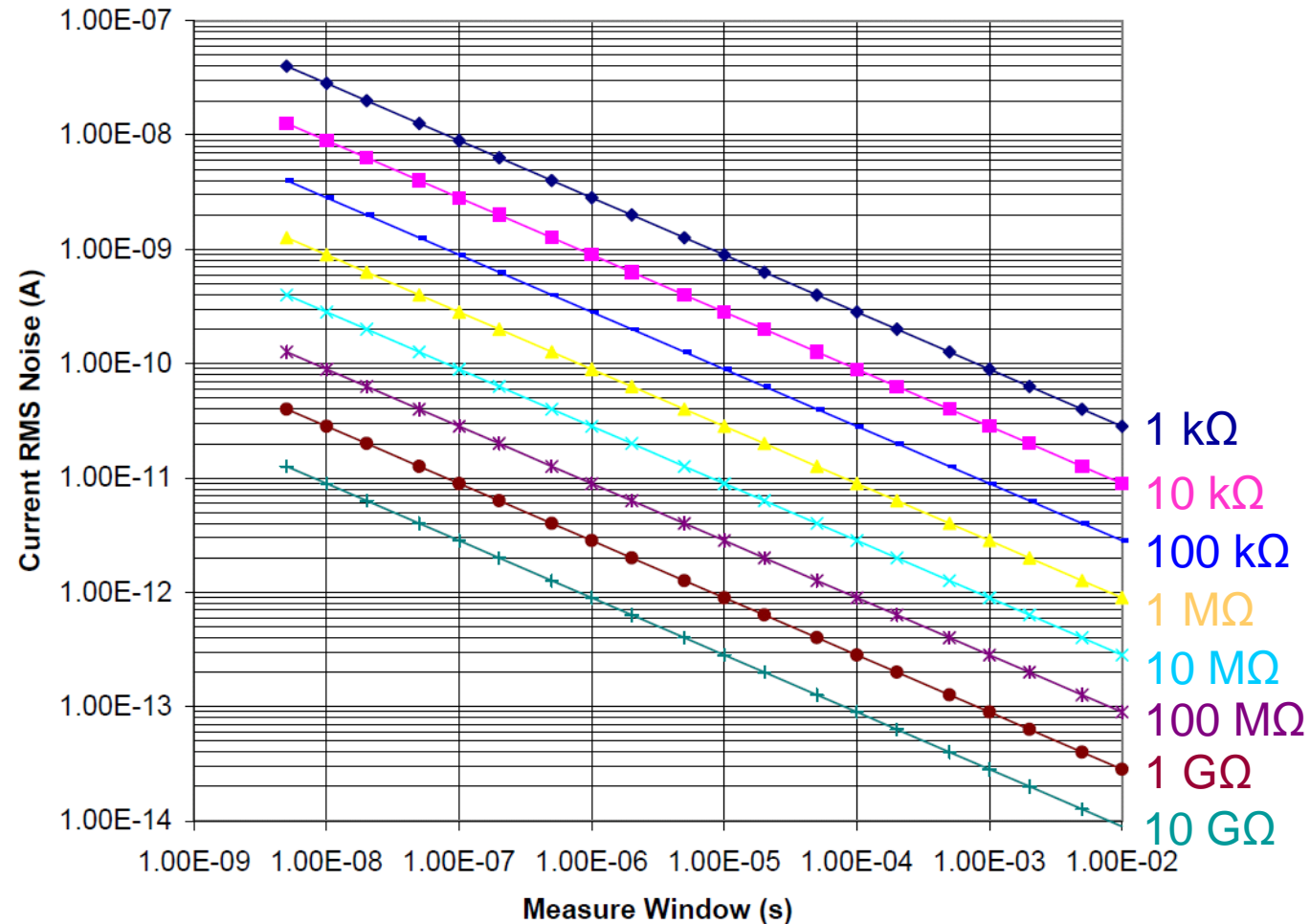
- It is impossible to measure low current (~nA) quickly (< 10us)
- Why?
  - Signal Level (number of electrons)
  - Noise
- Signal Level Example: Measure 5 nA in 1 ns
- Calculate the number of electrons for 5 nA during 1 ns window
  - $1 \text{ A} = 1 \text{ C/s} = 6.24 \times 10^{18} \text{ electrons/s}$
  - $5 \text{ nA} = (6.24 \times 10^{18} \text{ e/s}) * (5 \times 10^{-9}) = 31.2 \times 10^9 \text{ e/s}$
  - In 1 ns:  $(31.2 \times 10^9 \text{ e/s}) * (1 \times 10^{-9}) = 6.24 \times 10^2 \text{ e} = 31.2 \text{ electrons}$



# Johnson-Nyquist Noise vs Measure Window

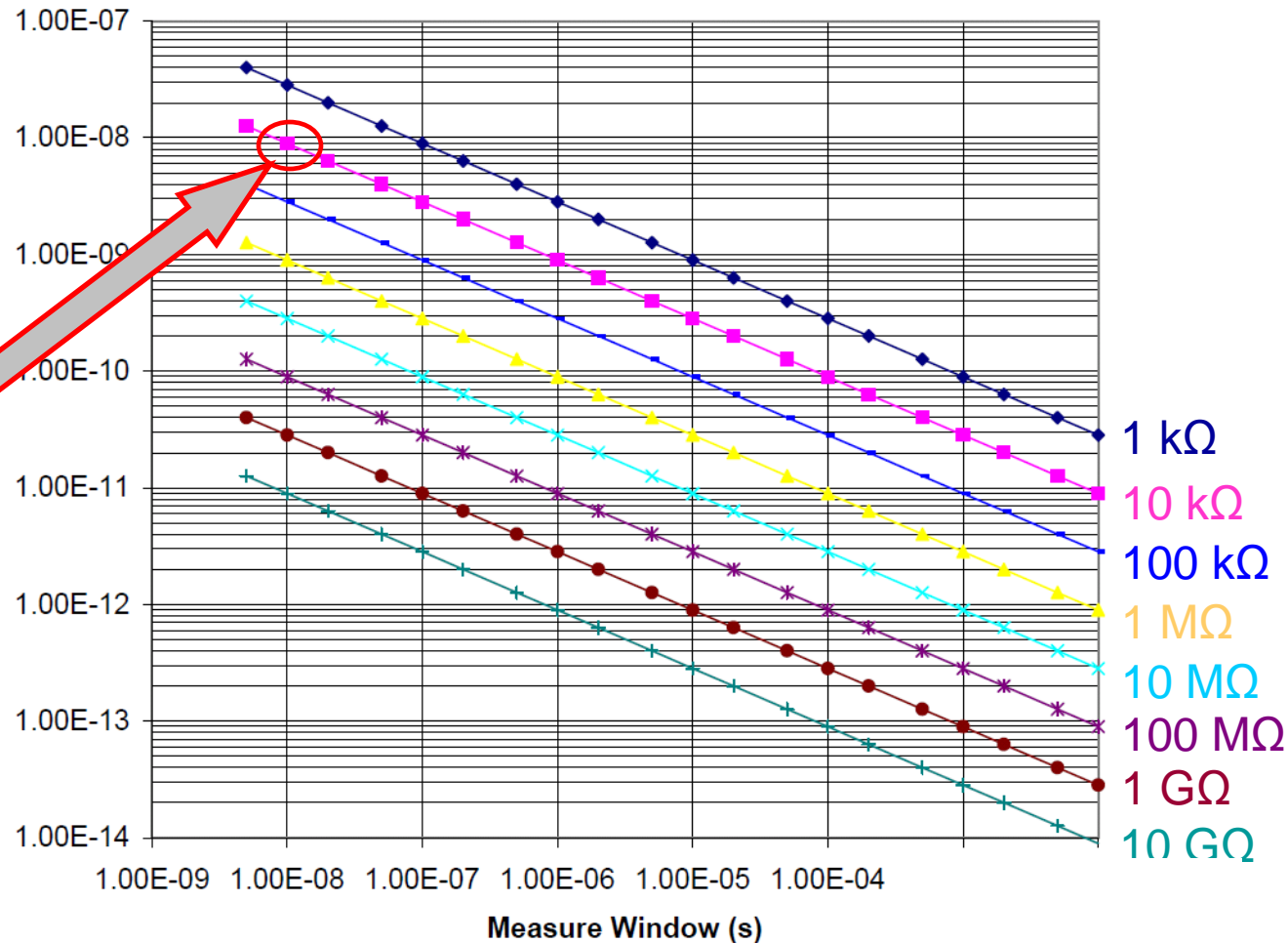
## • Johnson Noise

- Caused by electrons flowing through a resistance
- $V = \sqrt{4kTBR}$
- $I = \sqrt{4kTBR}/R$
- $k = 1.38E-23$  J/K, Boltzmann's constant
- $T = 290$  K
- $B = \text{Bandwidth} = 1/(2 \times \text{Measure Window})$
- $R = \text{Resistance}$



# Example: Johnson-Nyquist Noise vs Measure Window

- CMOS Transistor
- 10 k $\Omega$  drain-source channel
- Goal: Measure lowest possible current in 10 ns (spot mean window)
- Current Noise due to device alone = **10 nA RMS**
- 10 nA does not include any cable or instrument effects (each element in test system contributes Johnson noise)



# Conclusion

Further information about using the Model 4200, applications information, and measurement techniques is available:

- 1) [Model 4200 Reference Manual](#) – on CD, HELP menu, desktop
- 2) [Model 4200 Applications Manual](#) – on CD, HELP menu, desktop
- 3) [Applications Notes](#) – on CD, HELP menu, Keithley website, desktop
- 4) [Low Level Measurement Handbook](#) – can be requested from Keithley website
- 5) [Labview Drivers](#) – can be downloaded from Keithley website.
- 6) [Example Projects](#) – available from Keithley applications and in the projects folder – C:\S4200\kiuser\Projects
- 7) [External Instrument Libraries](#) – many already installed in KULT and others are available from Keithley applications

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